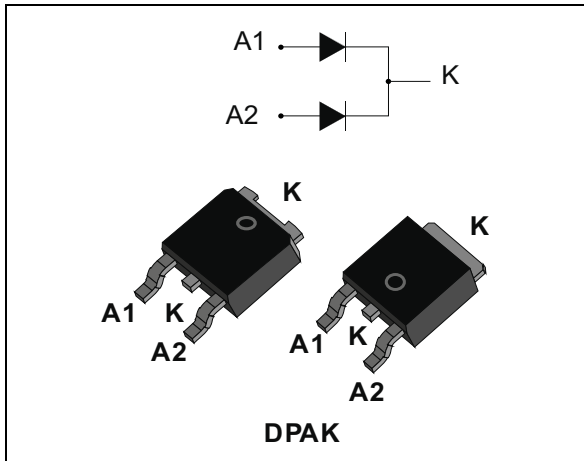


High efficiency ultrafast diode

Datasheet - production data



Description

Dual center tap rectifier suited for switched mode power supply and high frequency DC to DC converters.

Packaged in DPAK, this device is intended for use in low voltage, high frequency inverters, free-wheeling and polarity protection applications.

Table 1. Device summary

Symbol	Value
$I_{F(AV)}$	2 X 4A
V_{RRM}	200 V
T_j	175 °C
V_F (max)	0.95 V
t_{rr} (typ)	13 ns

Features

- Suited for SMPS
- Low losses
- Low forward and reverse recovery time
- High surge current capability
- High junction temperature
- ECOPACK^{®2} compliant component for DPAK on demand

1 characteristics

Table 2. Absolute ratings (limiting values at $T_j = 25\text{ °C}$ per diode, unless otherwise specified)

Symbol	Parameter	Value	Unit	
V_{RRM}	Repetitive peak reverse voltage	200	V	
$I_{F(RMS)}$	Forward rms current	10	A	
$I_{F(AV)}$	Average forward current, $\delta = 0.5$, square wave	$T_c = 155\text{ °C}$, per diode	4	A
		$T_c = 150\text{ °C}$, per device	8	
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ ms}$ sinusoidal	50	A
T_{stg}	Storage temperature range	-65 to + 175	°C	
T_j	Maximum operating junction temperature	175	°C	

Table 3. Thermal resistances

Symbol	Parameter	Value	Unit	
$R_{th(j-c)}$	Junction to case	Per diode	4	°C/W
		Total	2.5	
$R_{th(c)}$	Coupling	1.0		

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j(\text{diode } 1) = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$$

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25\text{ °C}$	$V_R = V_{RRM}$		4	μA
		$T_j = 125\text{ °C}$		2	40	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25\text{ °C}$	$I_F = 4\text{ A}$		1.1	V
		$T_j = 125\text{ °C}$		0.81	0.95	
		$T_j = 25\text{ °C}$	$I_F = 8\text{ A}$		1.25	V
		$T_j = 125\text{ °C}$		0.95	1.1	

1. Pulse test: $t_p = 5\text{ ms}$, $\delta < 2\%$

2. Pulse test: $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 0.80 \times I_{F(AV)} + 0.037 I_{F(RMS)}^2$$

Table 5. Dynamic characteristics (per diode)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$I_F = 0.5 \text{ A}$, $I_{RR} = 0.25 \text{ A}$, $I_R = 1 \text{ A}$, $T_j = 25 \text{ }^\circ\text{C}$		13	20	ns
t_{fr}	Forward recovery time	$I_F = 4 \text{ A}$, $di_F/dt = 100 \text{ A}/\mu\text{s}$ $V_{FR} = 1.1 \times V_{Fmax}$, $T_j = 25 \text{ }^\circ\text{C}$		50		ns
V_{FP}	Forward recovery voltage	$I_F = 4 \text{ A}$, $di_F/dt = 100 \text{ A}/\mu\text{s}$, $T_j = 25 \text{ }^\circ\text{C}$		2.4		V

Figure 1. Average forward power dissipation versus average forward current (per diode)

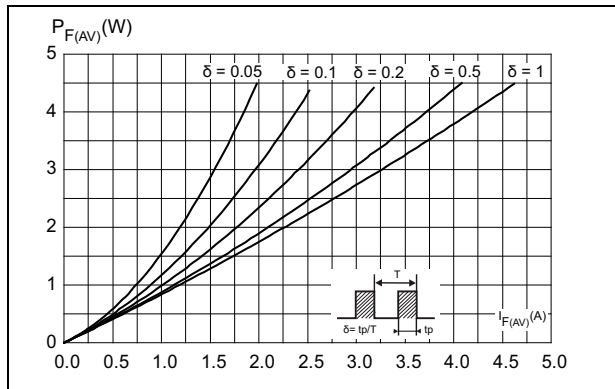


Figure 2. Forward voltage drop versus forward current (per diode)

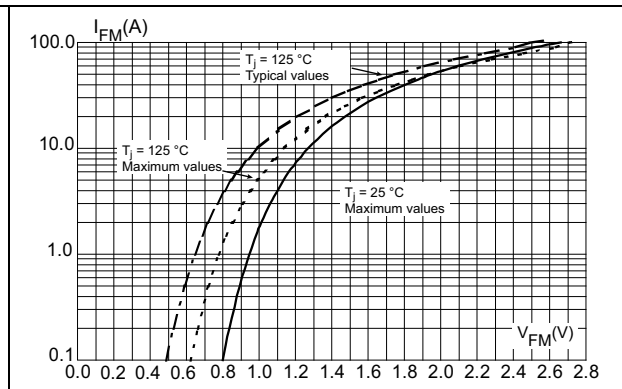


Figure 3. Relative variation of thermal impedance, junction to case, versus pulse duration

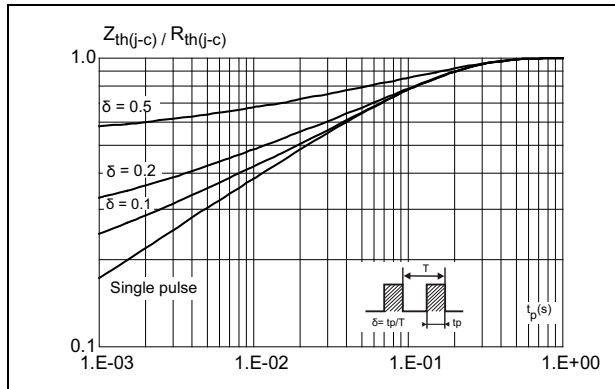


Figure 4. Junction capacitance versus reverse applied voltage (typical values, per diode)

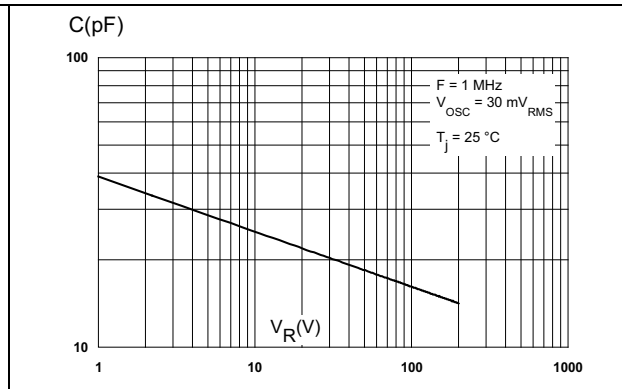


Figure 5. Reverse recovery charges versus di_F/dt (90% confidence, per diode)

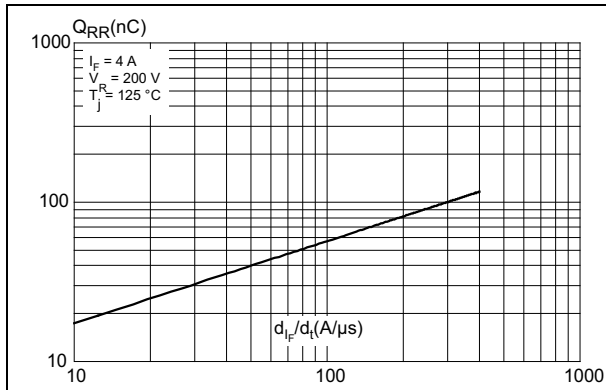


Figure 6. Peak reverse recovery current versus di_F/dt (90% confidence, per diode)

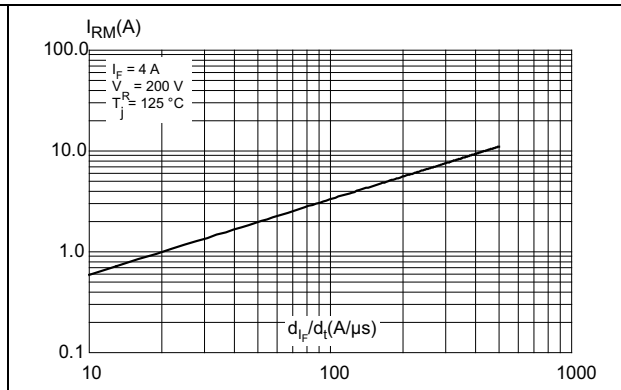


Figure 7. Dynamic parameters versus junction temperature

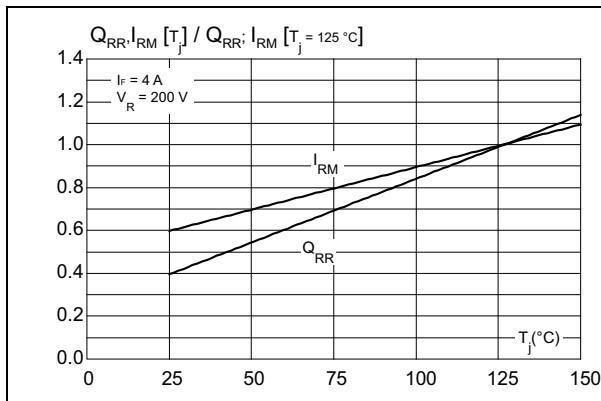
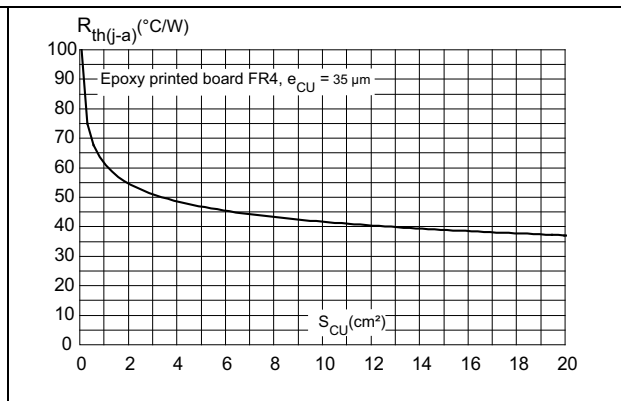


Figure 8. Thermal resistance, junction to ambient, versus copper surface under tab

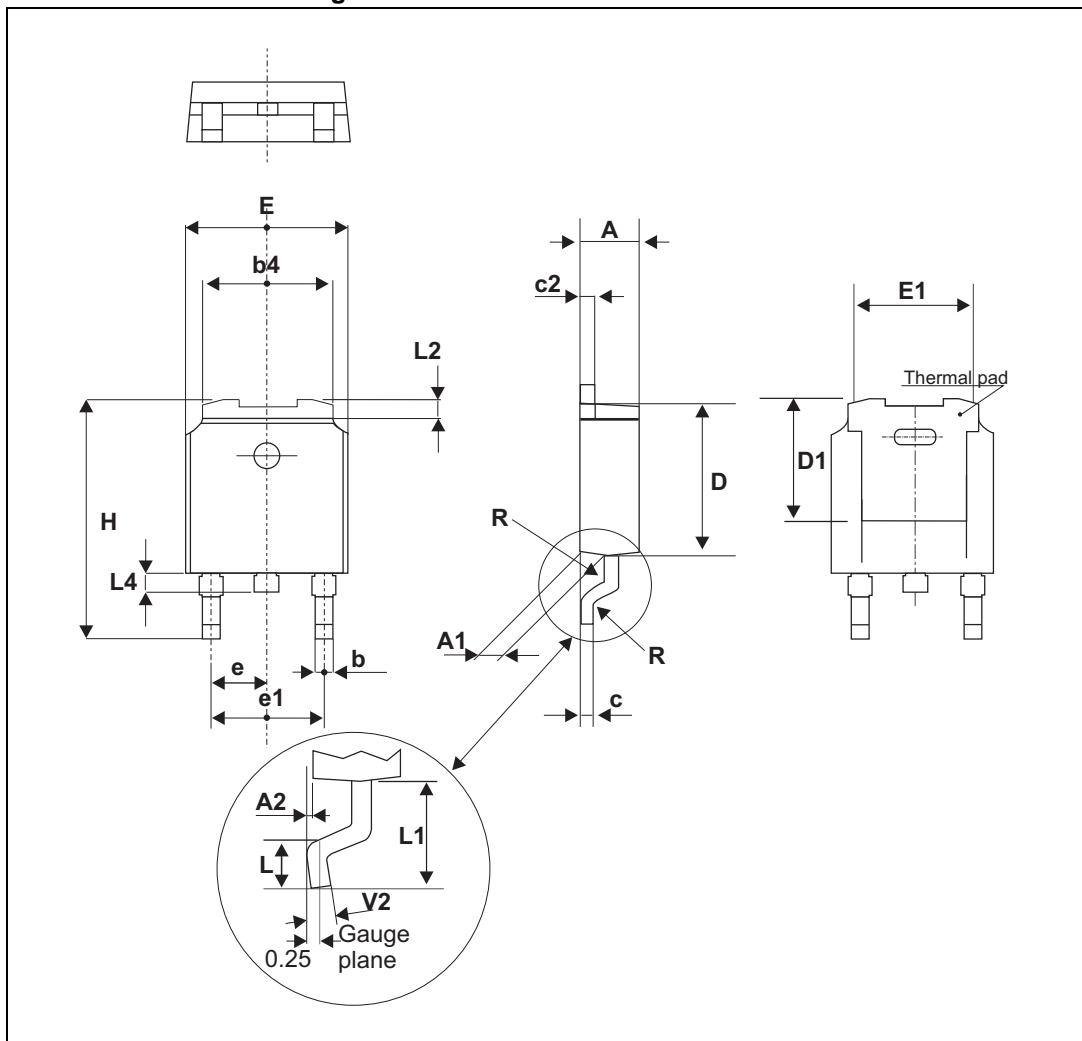


2 Package Information

- Epoxy meets UL94,V0
- Cooling method: by conduction (C)

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

Figure 9. DPAK dimension definitions

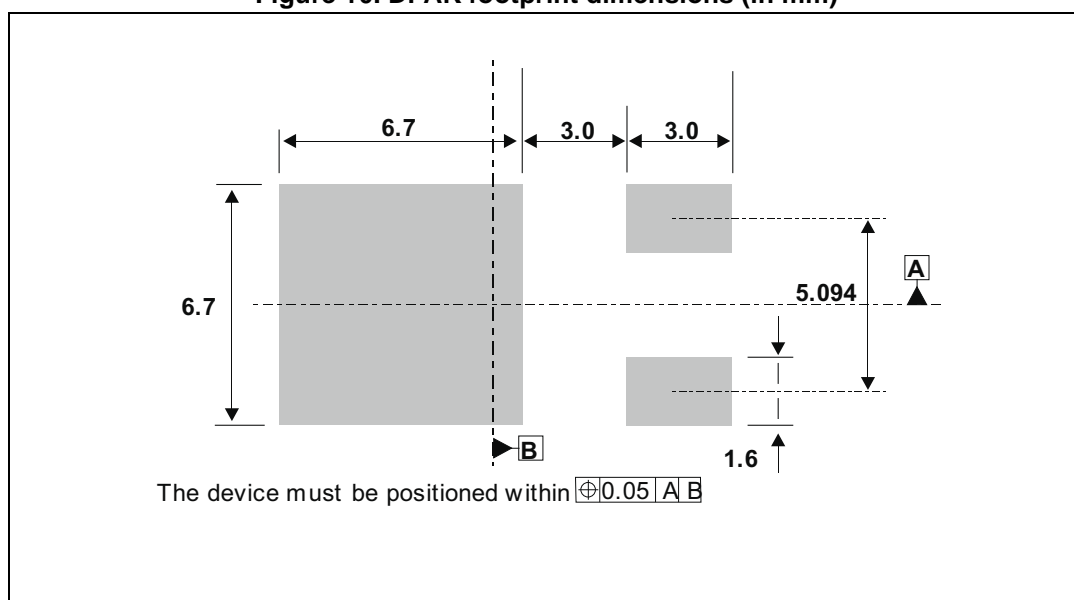


Note: This package drawing may slightly differ from the physical package. However, all the specified dimensions are guaranteed.

Table 6. DPAK dimension values

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.18		2.40	0.085		0.094
A1	0.90		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.01
b	0.64		0.90	0.025		0.035
b4	4.95		5.46	0.195		0.215
c	0.46		0.61	0.018		0.024
c2	0.46		0.60	0.018		0.024
D	5.97		6.22	0.235		0.245
D1	5.10			0.201		
E	6.35		6.73	0.250		0.265
E1	4.32			0.170		
e1	4.4		4.7	0.173		0.185
H	9.35		10.40	0.368		0.407
L	1.0		1.78	0.039		0.070
L2			1.27			0.05
L4	0.6		1.02	0.024		0.040
V2	0°		8°	0°		8°

Figure 10. DPAK footprint dimensions (in mm)



3 Ordering Information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH802CB-TR	STTH802CB	DPAK	0.3 g	2500	Tape and reel

4 Revision history

Table 8. Document revision history

Date	Revision	Description of Changes
04-Nov-2014	2	Removed TO-220AB and TO-220FPAB package information. Reformatted to current standard.

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